

SOT223 NPN SILICON PLANAR MEDIUM POWER DARLINGTON TRANSISTOR

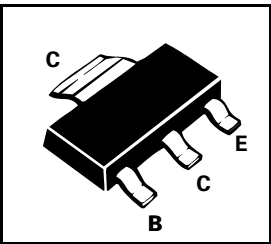
FZT600

ISSUE 3 – FEBRUARY 1997

FEATURES

- * 2A continuous current
- * 140 VOLT V_{CEO}
- * Guaranteed h_{FE} Specified up to 1A

PART MARKING DETAIL – FZT600



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	160	V
Collector-Emitter Voltage	V_{CEO}	140	V
Emitter-Base Voltage	V_{EBO}	10	V
Peak Pulse Current	I_{CM}	4	A
Continuous Collector Current	I_C	2	A
Power Dissipation	P_{tot}	2	W
Operating and Storage Temperature Range	$T_f; T_{stg}$	-55 to +150	°C

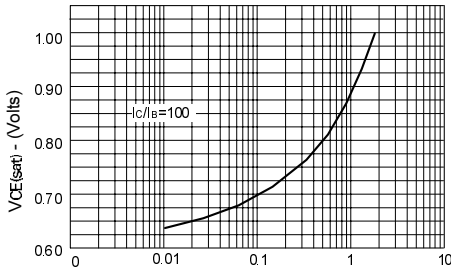
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	160			V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	140			V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	10			V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			0.01 10	μA μA	$V_{CB}=140\text{V}$ $V_{CB}=140\text{V}, T_{amb}=100^\circ\text{C}$
Collector Cut-Off Current	I_{CES}			10	μA	$V_{CES}=140\text{V}$
Emitter Cut-Off Current	I_{EBO}			0.1	μA	$V_{EB}=8\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.75 0.85	1.1 1.2	V V	$I_C=0.5\text{A}, I_B=5\text{mA}^*$ $I_C=1\text{A}, I_B=10\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.7	1.9	V	$I_C=1\text{A}, I_B=10\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		1.5	1.7	V	$I_C=1\text{A}, V_{CE}=5\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	1k 2k 1k		100k		$I_C=50\text{mA}, V_{CE}=10\text{V}^*$ $I_C=0.5\text{A}, V_{CE}=10\text{V}^*$ $I_C=1\text{A}, V_{CE}=10\text{V}^*$
		5k 10k 5k	10k 20k 10k	100k		$I_C=50\text{mA}, V_{CE}=10\text{V}^*$ $I_C=0.5\text{A}, V_{CE}=10\text{V}^*$ $I_C=1\text{A}, V_{CE}=10\text{V}^*$
Transition Frequency	f_T	150	250		MHz	$I_C=100\text{mA}, V_{CE}=10\text{V}$ $f=20\text{MHz}$
Output Capacitance	C_{obo}		10	15	MHz	$V_{CB}=10\text{V}, f=1\text{MHz}$
Switching Times	T_{on}		0.75		μs	$I_C=0.5\text{A}, V_{CE}=10\text{V}$
	T_{off}		2.20		μs	$I_{B1}=I_{B2}=0.5\text{mA}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
Spice parameter data is available upon request for this device

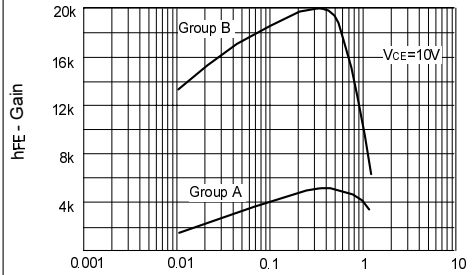
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TYPICAL CHARACTERISTICS



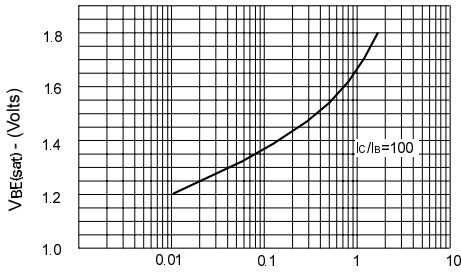
I_C - Collector Current (Amps)

$V_{CE(sat)}$ v I_C



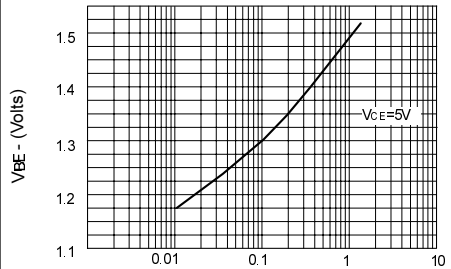
I_C - Collector Current (Amps)

h_{FE} v I_C



I_C - Collector Current (Amps)

$V_{BE(sat)}$ v I_C



I_C - Collector Current (Amps)

$V_{BE(on)}$ v I_C